

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	8379	(118/726,715,723).ocls.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/15 09:18
L3	250	(118/726,715,723).ocls. and electron beam and resistance	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/15 09:19
L4	17	(118/726,715,723).ocls. and (electron beam and resistance).clm.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/15 09:19
S1	7	(Itoh and Higuchi and Sakai and Honda and Takai and Okazaki and Inaba).in.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 09:50
S2	888313	Matsushita.as.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 09:59
S3	576436	(Matsushita Electric).as.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 09:59
S4	34558	(Matsushita Electric Industrial).as.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 09:59
S5	23206	Matsushita.as. and thin film	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 09:59
S6	1358	Matsushita.as. and thin film and electron beam	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 10:00

S7	528	Matsushita.as. and thin film and electron beam and heating	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 10:19
S8	15	Matsushita.as. and thin film and electron beam and resistive heating	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 10:19
S9	2	jp-01117208-\$.did.	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 10:22
S10	28	((118/726 or 118/715 or 118/723).cls. and ionizing and resistive heating	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 10:57
S11	38	((118/726 or 118/715 or 118/723).cls. and (electron beam or EB) and resistive heating	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 11:00
S12	113	((118/726 or 118/715 or 118/723).cls. and ((vapor ADJ5(electron beam or EB))	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 11:05
S13	127	((118/726 or 118/715 or 118/723).cls. and ((vapor or gas) ADJ5(electron beam or EB))	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 11:06
S14	82	((118/726 or 118/715 or 118/723).cls. and ((vapor or gas) ADJ5(electron beam or EB)) and heating	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 11:07
S15	1	("5436035").FN.	US-PGRUB; USPAT; USOCR	OR	OFF	2008/03/11 11:26
S16	2	(jp-58123867-\$.did.	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 16:30
S17	11	apparatus and ((resistance heating and electron beam) evaporation source)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/12 15:53

S18	3	(apparatus or machine or device) and ((resistance heating and electron beam evaporation source) and nozzle	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/12 16:01
S19	14	(apparatus or machine or device) and ((resistance heating and electron beam evaporation source)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/12 16:06
S20	33	(apparatus or machine or device) and ((resistance ADJ2 heating and electron ADJ2 beam) ADJ2 evaporation ADJ2 source)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/12 16:10
S21	5	(apparatus or machine or device) and ((resistance ADJ2 heating and electron ADJ2 beam) ADJ2 evaporation ADJ2 source) and nozzle	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/12 16:12
S22	9	(apparatus or machine or device) and ((resistance ADJ2 heating and electron ADJ2 beam) ADJ2 evaporation ADJ2 source) and (bias or negative)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/12 16:23
S23	20	(wada and nakagawa and hananaka).in.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/13 07:27
S24	9	(apparatus or machine or device) and ((resistance ADJ2 heating and electron ADJ2 beam) ADJ2 evaporation ADJ2 source) and (bias or negative or minus)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/13 07:38
S25	15	(apparatus or machine or device) and ((resistance ADJ2 heating and electron ADJ2 beam) ADJ4 evaporation ADJ2 source) and (bias or negative or minus)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/13 07:48
S26	239	(apparatus or machine or device) and ((resistance ADJ2 heating or electron ADJ2 beam) ADJ4 evaporation ADJ2 source) and (bias or negative or minus)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/13 07:49

S27	212	(apparatus or machine or device) and ((resistance ADJ2 heating or electron ADJ2 beam) ADJ2 evaporation ADJ2 source) and (bias or negative or minus)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/13 07:49
S28	9	(apparatus or machine or device) and ((resistance ADJ2 heating or electron ADJ2 beam) ADJ2 evaporation ADJ2 source) and ((bias or negative or minus) adj2 (source or device))	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/13 07:50
S29	1	("4394210").PN.	US-PGRUB; USPAT; USOCR	OR	OFF	2008/03/13 07:55
S30	65	(electron adj2 beam adj2 evaporation) and (resistance adj2 heating adj2 evaporation) and ((negative or bias) adj3 voltage)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/13 08:07
S31	7	(apparatus or machine or device) and ((resistance heating and electron beam evaporation source) and (nozzle or tube or port))	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/13 10:05
S32	12	(apparatus or machine or device) and ((resistance ADJ2 heating and electron ADJ2 beam) ADJ2 evaporation ADJ2 source) and (nozzle or tube)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/13 10:09
S33	1301	vacuum near2 (container or chamber) and electron near2 beam and resistance near2 heating	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/16 11:06
S34	261	vacuum near2 (container or chamber) and electron near2 beam and resistance near2 heating and bias	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/16 11:07
S35	45	vacuum near2 (container or chamber) and electron near2 beam and resistance near2 heating and bias and nozzle	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/16 11:07

S36	63	vacuum near2 (container or chamber) and electron near2 beam and resistance near2 heating and (118/726 or 118/715 or 118/723).ccls.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/16 11:13
S37	1	("20020001733").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/07/16 11:18
S38	149	(118/726 or 118/715 or 118/723).ccls. and electron and resistive heating	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/16 11:32
S39	12	(118/726 or 118/715 or 118/723).ccls. and electron same resistive same vacuum	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/16 11:33
S40	3343	ion\$6 adj2 assisted with deposition	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/16 11:45
S41	127	ion\$6 adj2 assisted with deposition and "118".clas.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/16 11:46
S42	42	(shinohara toshiro).in.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/16 16:09
S43	1080	electron beam with gas and ("118" or "427").clas.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/16 16:11
S44	24	electron beam with gas with path and ("118" or "427"). clas.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/16 16:11
S45	98	electron beam with gas same ionize\$ and ("118" or "427").clas.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/16 16:13
S46	110	electron beam with vapor same ionize\$ and ("118" or "427").clas.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/17 06:57

S47	184	bias voltage with surface same vapor deposit\$3	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/17 07:52
S48	489	bias voltage with (surface or substrate) same vapor deposit\$3	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/17 07:54
S49	129	bias voltage with (surface or substrate) same vapor deposit\$3 and ("118" or "427").clas.	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/17 07:55
S50	2824	electron beam same2 resistance heating	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/18 14:55
S51	2343	electron beam same2 resistance heating and deposition	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/18 14:55
S52	1717	electron beam same2 resistance heating and deposition near3 vapor	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/18 14:55
S53	859	electron beam same2 resistance heating and vacuum near3 (container or chamber or cavity)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/18 14:56
S54	782	electron beam same2 resistance heating and vacuum near3 (container or chamber or cavity) and metal	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/18 14:56
S55	83	electron beam same2 resistance heating and vacuum near3 (container or chamber or cavity) and metal and "118".clas.	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/18 14:57
S57	31	electron beam same2 resistance heating and vacuum near3 (container or chamber or cavity) and metal and 427/248.1.cds.	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/26 12:08

S58	428	(electron beam or EB) near4 evaporation and (EL panel or EL device)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/26 12:11
S59	147	(electron beam or EB) near4 evaporation and (EL panel or EL device) and (Sm or samarium)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/26 12:13
S60	66	(electron beam or EB) near4 evaporation same (Sm or samarium)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/26 12:13
S61	0	(electron beam or EB) near4 evaporation and ioniz \$3 same (Sm or samarium)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/26 12:14
S62	0	(electron beam or EB) near4 evaporation and ioniz \$4 same (Sm or samarium)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/26 12:14
S63	12	(electron beam or EB) near4 evaporation and ioniz \$4 same3 (Sm or samarium)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/26 12:15
S64	107	(electron beam or EB) near4 evaporation and ioniz \$4 and (Sm or samarium)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/26 12:16
S65	16	(electron beam or EB) near4 evaporation and ioniz \$4 and (Sm or samarium) and "427".clas.	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/26 12:16
S66	257	(electron beam or EB) near4 evaporation and ioniz \$4 and (Sm or samarium or Eu or europium or Dy or dysprosium or yb or ytterbium)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 06:28
S67	391	(electron beam or EB) near4 (evaporation or deposition) and ioniz\$4 and (Sm or samarium or Eu or europium or Dy or dysprosium or yb or ytterbium)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 06:36

S69	122	(electron beam or EB) near4 (evaporation or deposition) and ioniz\$4 and (Sm or samarium or Eu or europium or Dy or dysprosium or yb or ytterbium) and ("EL" or electroluminescen\$2)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 06:38
S70	1147	(electron beam or EB) near4 (evaporation or deposition) and (Sm or samarium or Eu or europium or Dy or dysprosium or yb or ytterbium) and ("EL" or electroluminescen\$2)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 06:45
S71	306	(electron beam or EB) near4 (evaporation or deposition) same2 (Sm or samarium or Eu or europium or Dy or dysprosium or yb or ytterbium) and ("EL" or electroluminescen\$2)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 06:46
S72	40	("3112197" "3173050" "3180703" "3180729" "3189447" "3240597" "3257203" "3382394" "3526501" "3542544" "3567450" "3615402" "3615404" "3658520" "3717462" "3820989" "4012376" "4127412" "4175961" "4232103" "4278746" "4539507" "4885211" "4950950").PN. OR ("5500568").URPN.	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/12/01 07:12
S73	149	(electron beam or EB) near4 (evaporation or deposition) same (Sm or samarium or Eu or europium or Dy or dysprosium or yb or ytterbium) and ("EL" or electroluminescen\$2)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 07:31
S74	408	(electron beam or EB) same (Sm or samarium or Eu or europium or Dy or dysprosium or yb or ytterbium) and ("EL" or electroluminescen\$2)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 08:03

S75	2609	118/726.cds.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 08:07
S76	423	118/726.cds. and electron beam	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 08:07
S77	29	118/726.cds. and electron beam and (Sm or samarium or Eu or europium or Dy or dysprosium or yb or ytterbium)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 08:10
S78	62	118/726.cds. and (Sm or samarium or Eu or europium or Dy or dysprosium or yb or ytterbium)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 08:15
S79	147	118/726.cds. and electron beam and resistance	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 08:18
S80	1741	electron beam same (Sm or samarium or Eu or europium or Dy or dysprosium or yb or ytterbium)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 08:22
S81	532	electron beam same (samarium or europium or dysprosium or ytterbium)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 08:22
S82	207	electron beam same (samarium or europium or dysprosium or ytterbium) same (ioniz\$5 or activat\$3)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 08:23
S83	25	electron beam same (samarium or europium or dysprosium or ytterbium) same (ioniz\$5)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 08:23
S84	152	electron beam same (samarium or europium or dysprosium or ytterbium) same (vapor or gas)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 08:24

S85	1	(electron beam or EB) same (Sm or samarium or Eu or europium or Dy or dysprosium or yb or ytterbium) adj2 (gas or vapor) and ("EL" or electroluminescen\$2)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 08:27
S87	44	(electron beam or EB) same (Sm or samarium or Eu or europium or Dy or dysprosium or yb or ytterbium) and ("EL" or electroluminescen\$2) and "427".clas.	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 08:28
S88	7	(electron beam or EB) same (Sm or samarium or Eu or europium or Dy or dysprosium or yb or ytterbium) evaporat\$3	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 08:43
S89	354	(electron beam or EB) same (Sm or samarium or Eu or europium or Dy or dysprosium or yb or ytterbium) same evaporat\$3	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 08:44
S90	56	(yano yoshihiko).in. and electron beam	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 09:14
S91	10	("20020122895" "4547703" "4847609" "5602445" "6072198" "6218774" "6242858" "6403204" "6447654").PN. OR ("6699596").URFN.	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/12/01 09:20
S92	14	118/726.ccls. and electron beam same (magnesium or Mg)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 09:27
S93	164	electron beam same magnesium and electroluminescen\$2	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 09:29
S94	23	electron beam same magnesium and (electroluminescen\$2 or "EL") and "427".clas.	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 09:33

S95	37	electron beam same (magnesium or "Mg") and (electroluminescen\$2 or "EL") and "427".clas.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 09:36
S96	15	(electron beam or EB) with (magnesium or "Mg") and (electroluminescen\$2 or "EL") and "427".clas.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 09:36
S97	2	(jp-63079959-\$).did.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 09:40
S98	48	118/726.ccls. and electron beam and magnesium	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 09:45
S99	9	("4268711" "4385083"). PN. OR ("5004721").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/01 10:31
S100	99	(electron beam or EB or e-beam) adj3 (co-evaporation or coevaporation)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 10:53
S102	67	(electron beam or EB or e-beam) adj3 (co-evaporation or coevaporation) and resistance	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 10:54
S103	254	(electron beam or EB or e-beam) near4 (barium or "ba")	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 10:56
S104	61	118/726.ccls. and (cobalt or "co") and (lithium or "li")	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 11:10
S105	58	118/726.ccls. and (cobalt or "co") and (lithium or "li")	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/12/01 11:10
S106	20	("4314874" "4333226" "4351712" "4634600" "4855013" "4861750").PN. OR ("5016563").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/01 11:18

S107	77	118/726.ccls. and (electron beam or EB or e-beam) and resistance and (silicon or "S")	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/01 11:38
S108	26	("2752882" "2845894" "2938816" "3446936" "3583361" "3926508" "4082636" "4098919").PN. OR ("4197814").URPN.	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/12/01 11:48
S109	17	("3326718" "3549416" "4129166" "4197573" "4197814" "4213844" "4692230" "4793908" "4861750" "4882023" "4950642").PN. OR ("5079224").URPN.	US-PGRUB; USPAT; USOCR	ADJ	ON	2008/12/02 06:35
S110	153	ioniz\$3 with (Sm or samarium or Eu or europium or Dy or dysprosium or yb or ytterbium)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 06:37
S111	34	ioniz\$3 with (Sm or samarium or Eu or europium or Dy or dysprosium or yb or ytterbium) and thin film	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 06:37
S112	9	ioniz\$3 with (Sm or samarium or Eu or europium or Dy or dysprosium or yb or ytterbium) and "427".clas.	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 06:39
S113	398	electron beam adj2 \$2evaporation and yttrium and barium and copper	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 06:53
S114	76	electron beam adj2 \$2evaporation and yttrium and barium and copper and "427".clas.	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 06:54
S115	10	electron beam adj2 \$2evaporation and yttrium and barium and copper and "118".clas.	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 06:55
S116	71	electron beam adj2 \$2evaporation and 118/726.ccls.	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 06:55

S117	29	(electron beam or EB or e-beam) adj2 \$2evaporation and yttrium and copper and "118".clas.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 07:11
S118	198	(electron beam or EB or e-beam) adj2 \$2evaporation and thin film and "118".clas.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 08:21
S119	819	(118/726 or 118/715 or 118/723).cls. and electron and (resistance or resistive)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 11:04
S120	462	(118/726 or 118/715 or 118/723).cls. and electron and (resistance or resistive) and thin film	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/03 12:31
S121	72	(118/726 or 118/715 or 118/723).cls. and continuous and super \$1conduct\$4	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/05 06:14
S122	65	continuous same super \$1conduct\$4 and evaporation and (roll or drum)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/05 06:15
S123	26	("4430366" "4861750").PN. OR ("5017550").URFN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/05 06:17
S124	25	("4486464" "4714047" "5017550").PN. OR ("5185178").URFN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/05 06:19
S125	4	continuous web and super \$1conduct\$4 and evaporation	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/05 06:36
S126	1996	continuous and super \$1conduct\$4 and evaporation	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/05 06:36
S127	86	continuous and super \$1conduct\$4 and evaporation and "118".clas.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/05 06:36

S128	422	continuous and super \$1conduct\$4 and evaporation and (roll or drum)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/05 06:37
S129	16	continuous and super \$1conduct\$4 and evaporation and (roll or drum) and "118".clas.	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/05 06:37
S130	7	continuous same2 super \$1conduct\$4 and evaporation and (roll or drum) and "118".clas.	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/05 07:04
S131	7	(118/726 or 118/715 or 118/723).cls. and continuous and super \$1conduct\$4 and (roll or drum)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/05 07:05
S132	10	(118/726 or 118/715 or 118/723).cls. and super \$1conduct\$4 and (roll or drum)	US-PGRUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/05 07:05

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